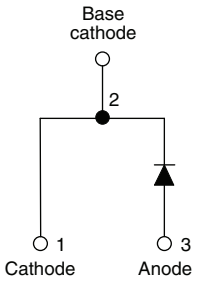
HEXFRED®
Ultrafast Soft Recovery Diode, 30 A



TO-247AC 2L



FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Pb-free
RoHS COMPLIANT
HALOGEN FREE

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA30PB120... is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 30 A continuous current, the VS-HFA30PB120... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA30PB120... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

PRIMARY CHARACTERISTICS	
$I_{F(AV)}$	30 A
V_R	1200 V
V_F at I_F	2.3 V
t_{rr} typ.	47 ns
T_J max.	150 °C
Package	TO-247AC 2L
Circuit configuration	Single

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Cathode to anode voltage	V_R		1200	V
Maximum continuous forward current	I_F	T_C = 100 °C	30	A
Single pulse forward current	I_{FSM}	t_p = 10 ms	120	
Maximum repetitive forward current	I_{FRM}		90	
Maximum power dissipation	P_D	T_C = 25 °C	350	W
		T_C = 100 °C	140	
Operating junction and storage temperature range	T_J, T_{Stg}		-55 to +150	°C

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ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V_{BR}	I_R = 100 µA		1200	-	-	V
Maximum forward voltage	V_{FM}	I_F = 30 A	See fig. 1	-	2.4	4.1	
		I_F = 60 A		-	3.1	5.7	
		I_F = 30 A, T_J = 125 °C		-	2.3	4.0	
Maximum reverse leakage current	I_{RM}	V_R = V_R rated	See fig. 2	-	1.3	40	µA
		T_J = 125 °C, V_R = 0.8 x V_R rated		-	1100	4000	
Junction capacitance	C_T	V_R = 200 V	See fig. 3	-	50	75	pF
Series inductance	L_S	Measured lead to lead 5 mm from package body		-	8.0	-	nH

DYNAMIC RECOVERY CHARACTERISTICS (T_J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time See fig. 5, 10	t_{rr}	I_F = 1.0 A, dI_F/dt = 200 A/µs, V_R = 30 V		-	47	-	ns
	t_{rr1}	T_J = 25 °C	I_F = 30 A dI_F/dt = 200 A/µs V_R = 200 V	-	110	170	
	t_{rr2}	T_J = 125 °C		-	170	260	
Peak recovery current See fig. 6	I_{RRM1}	T_J = 25 °C		-	10	15	A
	I_{RRM2}	T_J = 125 °C		-	16	24	
Reverse recovery charge See fig. 7	Q_{rr1}	T_J = 25 °C		-	650	980	nC
	Q_{rr2}	T_J = 125 °C		-	1540	2310	
Peak rate of fall of recovery current during t_b See fig. 8	$dI_{(rec)M}/dt1$	T_J = 25 °C		-	270	-	A/µs
	$dI_{(rec)M}/dt2$	T_J = 125 °C		-	240	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	T_{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Thermal resistance, junction to case	R_{thJC}		-	-	0.36	°C/W
Thermal resistance, junction to ambient	R_{thJA}	Typical socket mount	-	-	40	
Thermal resistance, case to heatsink	R_{thCS}	Mounting surface, flat, smooth, and greased	-	0.50	-	
Weight			-	5.61	-	g
			-	0.198	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-247AC 2L	HFA30PB120			

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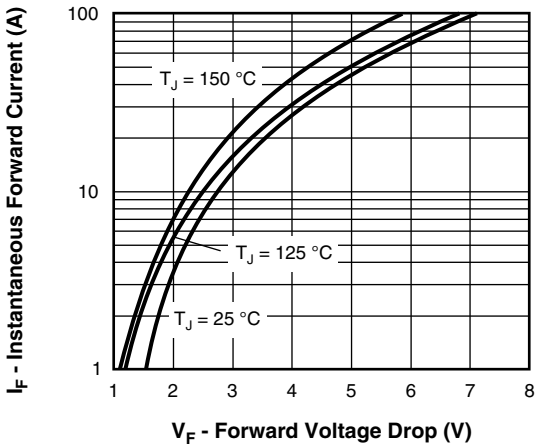


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

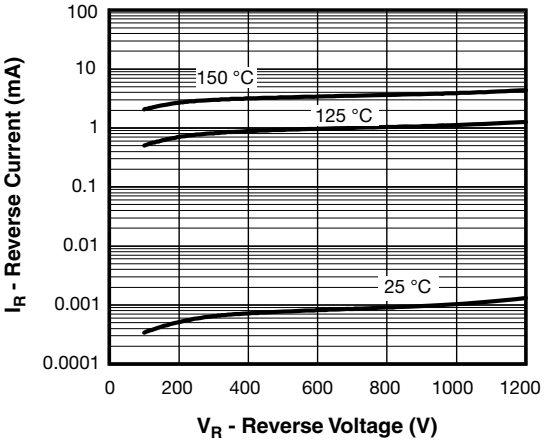


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

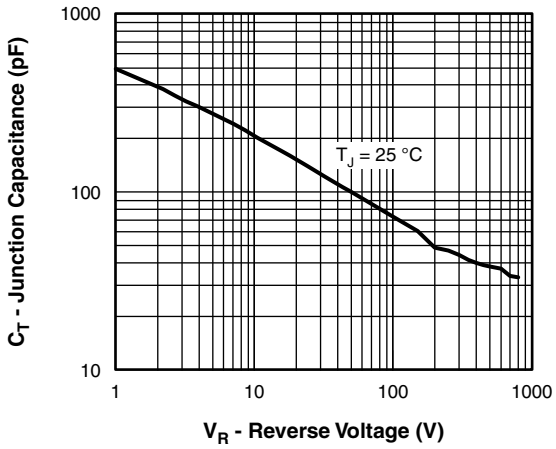


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

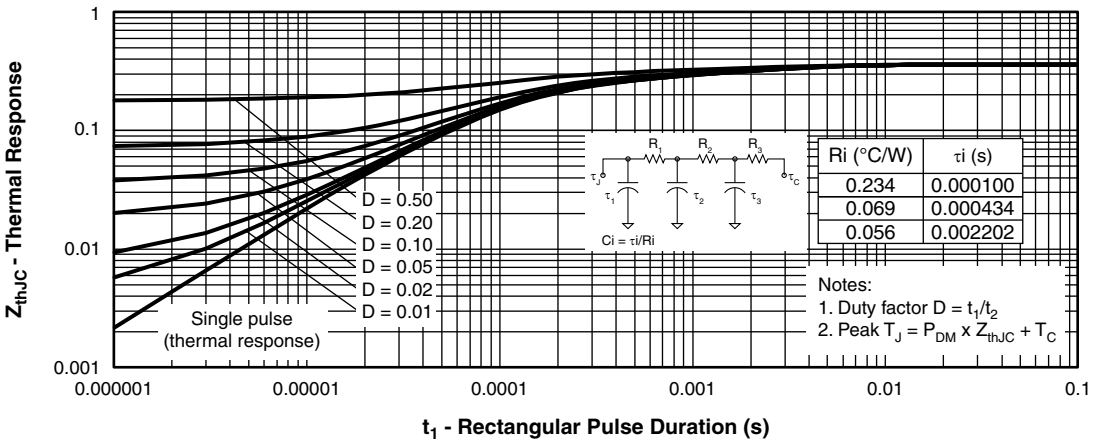


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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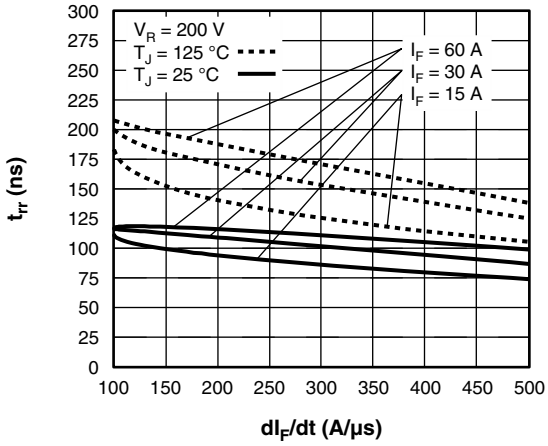


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt (Per Leg)

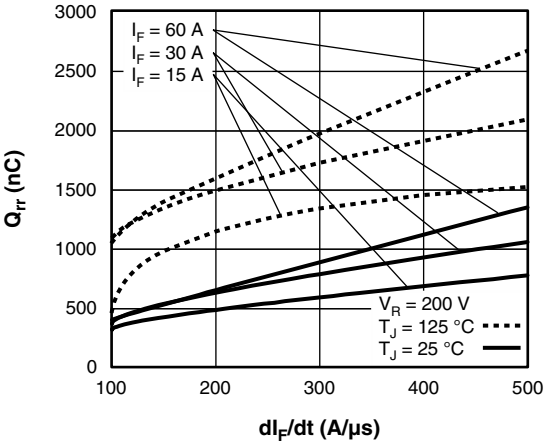


Fig. 7 - Typical Stored Charge vs. dI_F/dt (Per Leg)

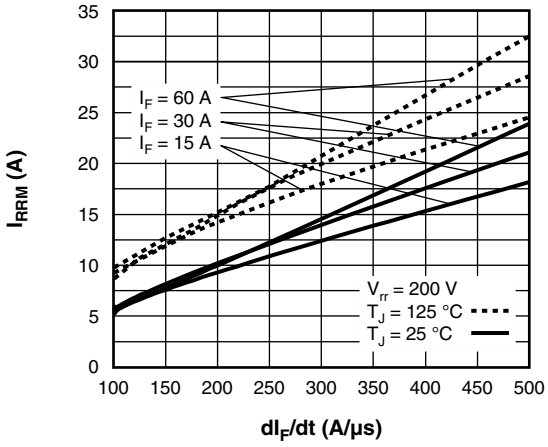


Fig. 6 - Typical Recovery Current vs. dI_F/dt (Per Leg)

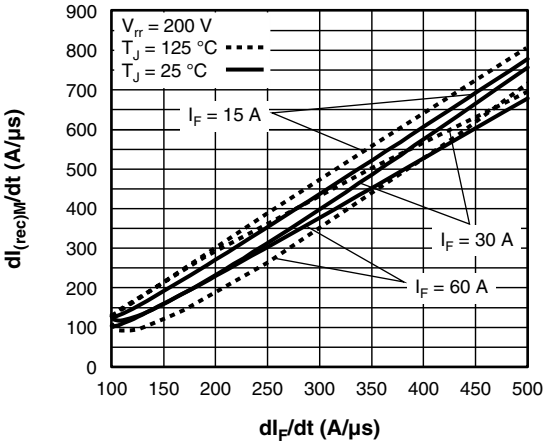
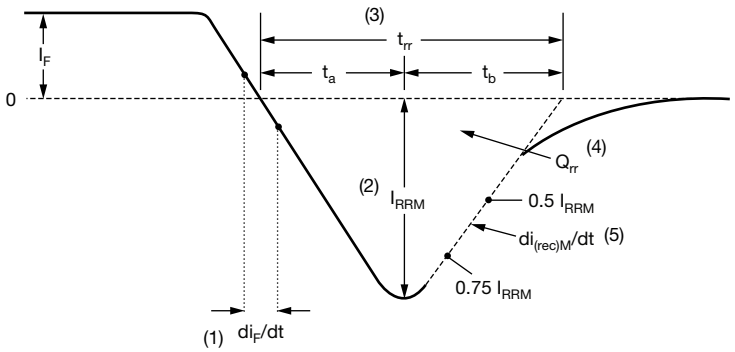


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt(Per Leg)



(1) di_F/dt - rate of change of current through zero crossing

(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

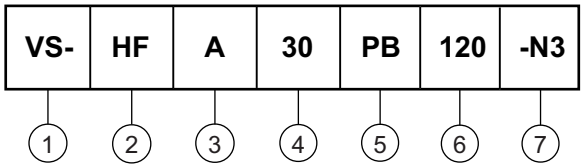
(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product
2 - HEXFRED® family
3 - Electron irradiated
4 - Current rating (30 = 30 A)
5 - PB = TO-247AC, 2 pins
6 - Voltage rating: (120 = 1200 V)
7 - Environmental digit:
-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

ORDERING INFORMATION (Example)			
PREFERRED P/N	**QUANTITY PER T/R**	**MINIMUM ORDER QUANTITY**	**PACKAGING DESCRIPTION**
VS-HFA30PB120-N3	25	500	Antistatic plastic tube

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96144
Part marking information	www.vishay.com/doc?95648

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